

2SJ518

Silicon P Channel MOS FET

REJ03G0875-0400
(Previous: ADE-208-580B)
Rev.4.00
Sep 07, 2005

Description

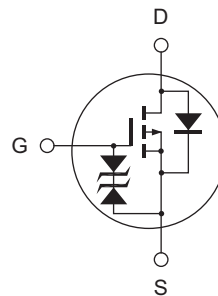
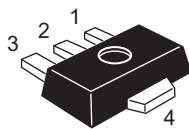
High speed power switching

Features

- Low on-resistance
 $R_{DS(on)} = 0.35 \Omega$ typ. (at $V_{GS} = -10 \text{ V}$, $I_D = -1 \text{ A}$)
- Low drive current
- 4 V gate drive devices
- High speed switching

Outline

RENESAS Package code: PLZZ0004CA-A
(Package name: UPAK®)



1. Gate
2. Drain
3. Source
4. Drain

Note: Marking is "AZ".

*UPAK is a trademark of Renesas Technology Corp.

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Value	Unit
Drain to source voltage	V _{DSS}	-60	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	-2	A
Drain peak current	I _{D (pulse)} ^{Note 1}	-4	A
Body to drain diode reverse drain current	I _{DR}	-2	A
Avalanche current	I _{AP} ^{Note 2}	-2	A
Avalanche energy	E _{AR}	0.34	mJ
Channel dissipation	P _{ch} ^{Note 3}	1	W
Channel temperature	T _{ch}	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

Notes: 1. PW ≤ 10 μs, duty cycle ≤ 1%

2. Value at T_{ch} = 25°C, R_g ≥ 50 Ω

3. Value at when using the aluminum ceramic board (12.5 × 20 × 0.7 mm)

Electrical Characteristics

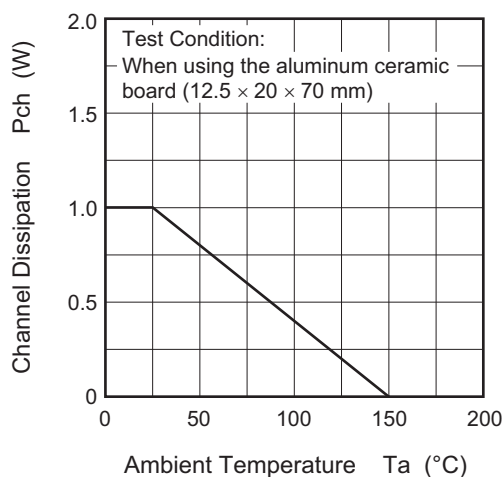
(Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	V _{(BR) DSS}	-60	—	—	V	I _D = -10 mA, V _{GS} = 0
Gate to source breakdown voltage	V _{(BR) GSS}	±20	—	—	V	I _G = ±100 μA, V _{DS} = 0
Zero gate voltage drain current	I _{DSS}	—	—	-10	μA	V _{DS} = -60 V, V _{GS} = 0
Gate to source leak current	I _{GSS}	—	—	±10	μA	V _{GS} = ±16 V, V _{DS} = 0
Gate to source cutoff voltage	V _{GS (off)}	-1.0	—	-2.0	V	I _D = -1 mA, V _{DS} = -10 V
Static drain to source on state resistance	R _{DS (on)}	—	0.35	0.46	Ω	I _D = -1 A, V _{GS} = -10 V ^{Note 4}
	R _{DS (on)}	—	0.45	0.63	Ω	I _D = -1 A, V _{GS} = -4 V ^{Note 4}
Forward transfer admittance	y _{fs}	1.2	2.0	—	S	I _D = -1 A, V _{DS} = -10 V ^{Note 4}
Input capacitance	C _{iss}	—	220	—	pF	V _{DS} = -10 V
Output capacitance	C _{oss}	—	110	—	pF	V _{GS} = 0
Reverse transfer capacitance	C _{rss}	—	35	—	pF	f = 1 MHz
Turn-on delay time	t _{d (on)}	—	10	—	ns	V _{GS} = -10 V I _D = -1 A R _L = 30 Ω
Rise time	t _r	—	11	—	ns	
Turn-off delay time	t _{d (off)}	—	45	—	ns	
Fall time	t _f	—	30	—	ns	
Body to drain diode forward voltage	V _{DF}	—	-1.05	—	V	I _F = -2 A, V _{GS} = 0
Body to drain diode reverse recovery time	t _{rr}	—	50	—	ns	I _F = -2 A, V _{GS} = 0 di _F /dt = 50 A/μs

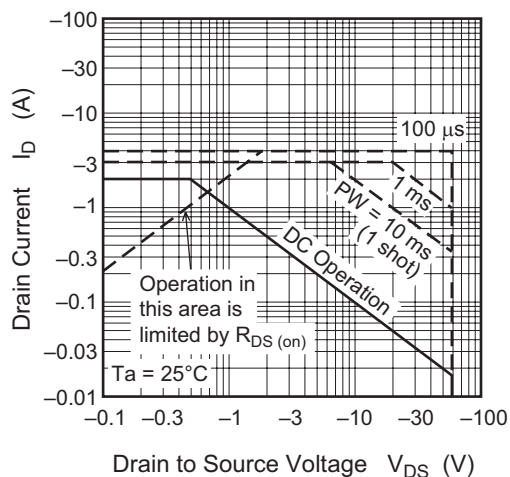
Note: 4. Pulse test

Main Characteristics

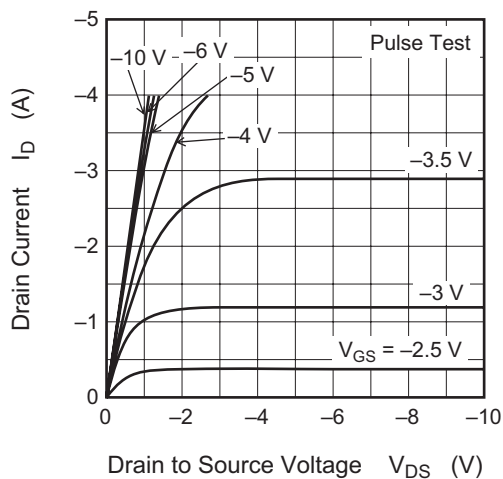
Power vs. Temperature Derating



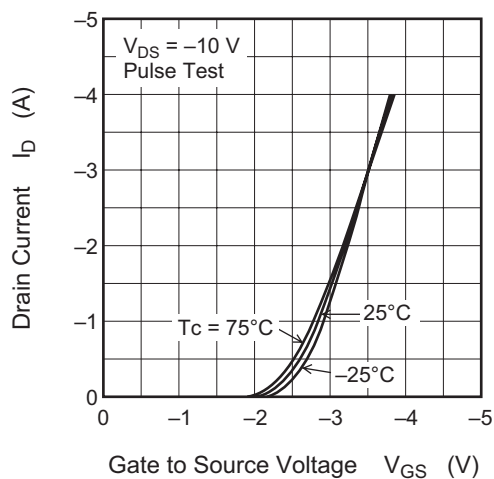
Maximum Safe Operation Area



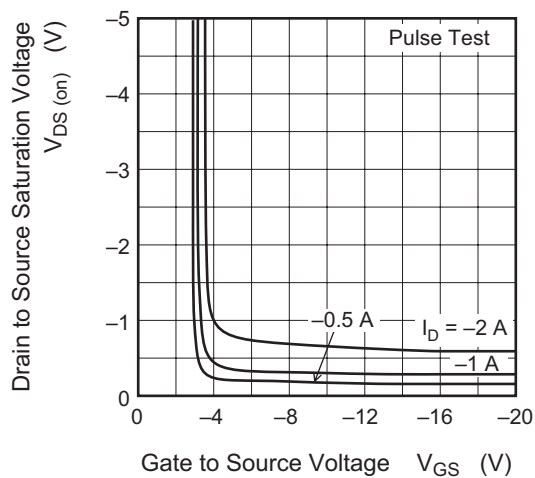
Typical Output Characteristics



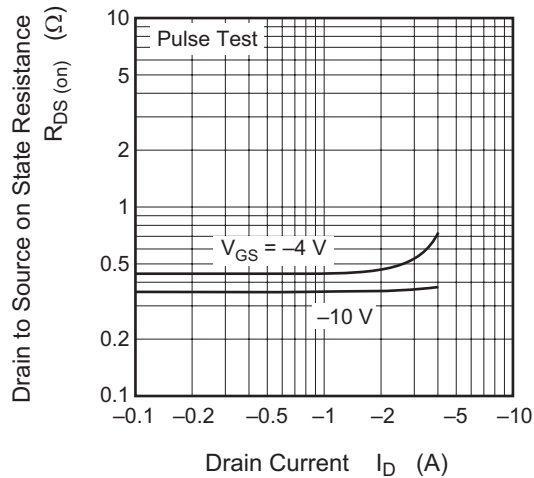
Typical Transfer Characteristics

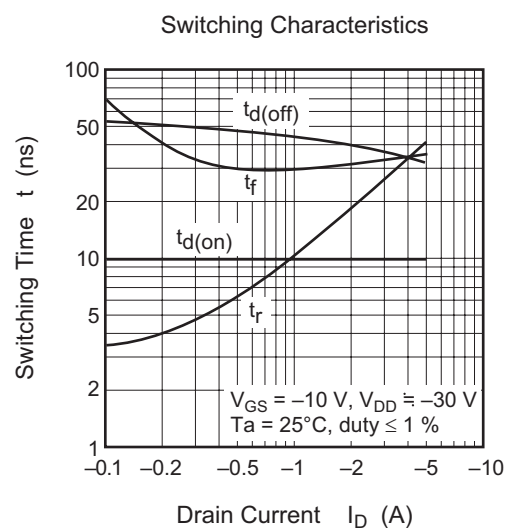
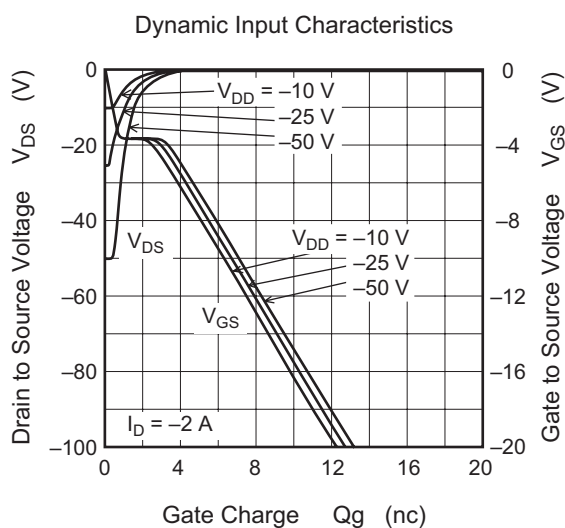
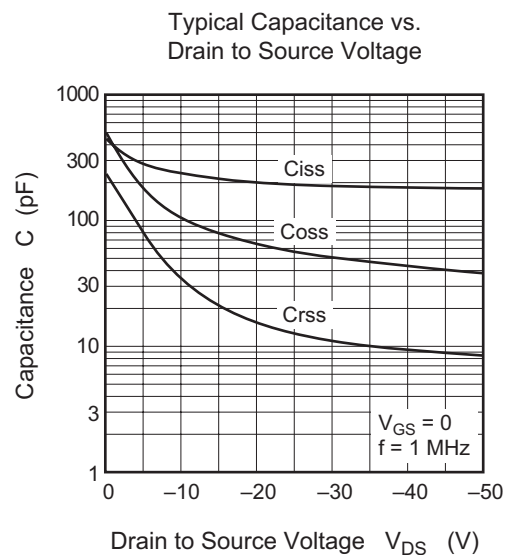
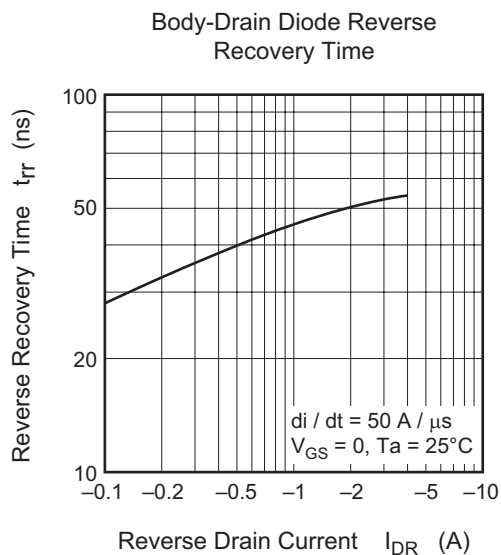
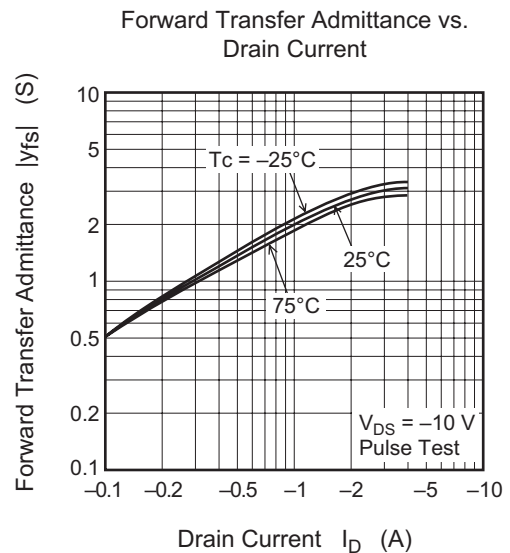
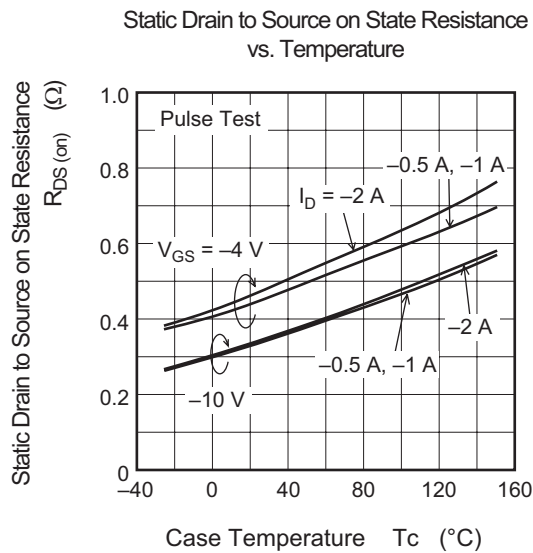


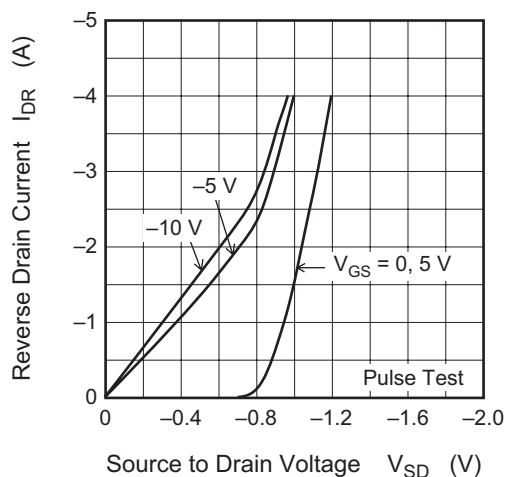
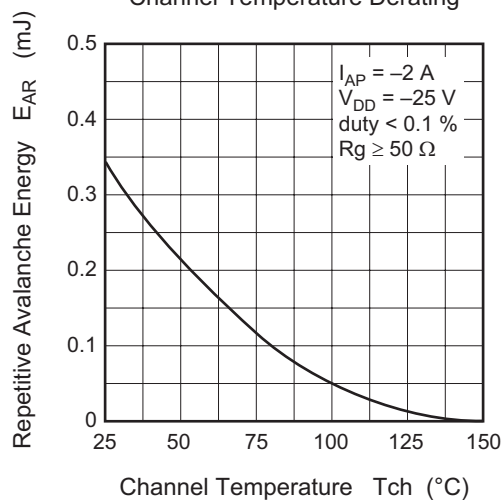
Drain to Source Saturation Voltage vs. Gate to Source Voltage



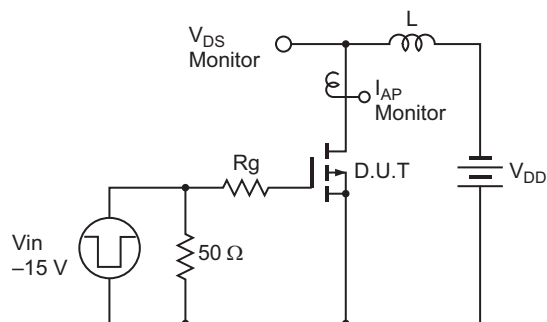
Static Drain to Source on State Resistance vs. Drain Current



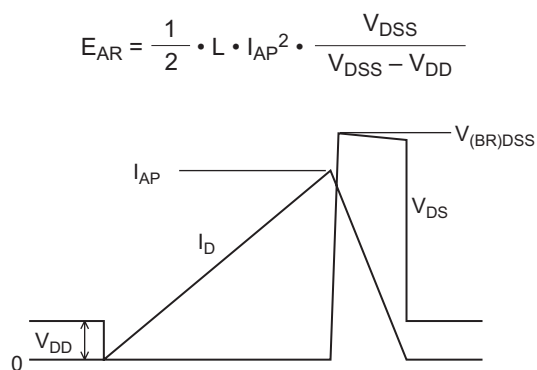


Reverse Drain Current vs.
Source to Drain VoltageMaximum Avalanche Energy vs.
Channel Temperature Derating

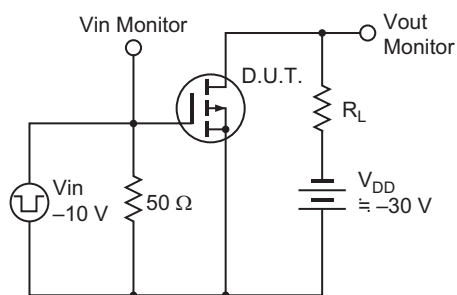
Avalanche Test Circuit



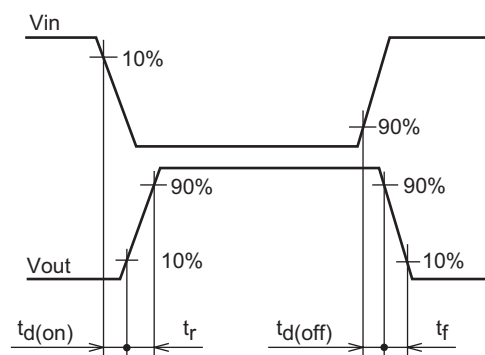
Avalanche Waveform



Switching Time Test Circuit



Waveform



Package Dimensions

JEITA Package Code	RENEAS Code	Package Name	MASS[Typ.]	Unit: mm
SC-62	PLZZ0004CA-A	UPAK / UPAKV	0.050g	

The drawing shows three views of the package:

- Top View:** Overall width is 4.5 ± 0.1 mm. The central mounting pad has a diameter of $\phi 1$ mm. The distance from the center to the side leads is 1.5 ± 0.1 mm. The lead width is 0.53 mm Max and 0.48 mm Max. The distance between the two side leads is 3.0 mm. The distance from the center to the bottom lead is 1.5 mm. The bottom lead width is 0.8 mm Min.
- Side View:** The package height is 1.5 ± 0.1 mm. The lead height is 0.44 mm Max. The distance from the base to the top of the package is 0.4 mm.
- Front View:** The package width is 1.5 mm. The lead width is 0.4 mm. The distance from the base to the top of the package is 0.2 mm.

Ordering Information

Part Name	Quantity	Shipping Container
2SJ518AZTL-E	1000 pcs	Taping
2SJ518AZTR-E	1000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A
Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited

Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K.
Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology Hong Kong Ltd.

7th Floor, North Tower, World Finance Centre, Harbour City, 1 Canton Road, Tsimshatsui, Kowloon, Hong Kong
Tel: <852> 2265-6688, Fax: <852> 2730-6071

Renesas Technology Taiwan Co., Ltd.

10th Floor, No.99, Fushing North Road, Taipei, Taiwan
Tel: <886> (2) 2715-2888, Fax: <886> (2) 2713-2999

Renesas Technology (Shanghai) Co., Ltd.

Unit2607 Ruijing Building, No.205 Maoming Road (S), Shanghai 200020, China
Tel: <86> (21) 6472-1001, Fax: <86> (21) 6415-2952

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632
Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd.

Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea
Tel: <82> 2-796-3115, Fax: <82> 2-796-2145

Renesas Technology Malaysia Sdn. Bhd.

Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia
Tel: <603> 7955-9390, Fax: <603> 7955-9510